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Team Nexperia



PMBTA45

500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

Rev. 02 — 10 March 2010 Product data she Product data sheet

Product profile 1.

1.1 General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9050T.

1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

1.3 Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|--------------------------------|--|-----|-----|------|------|
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0 V$ | - | - | 500 | V |
| V_{CEO} | collector-emitter voltage | open base | - | - | 500 | V |
| I _C | collector current | | - | - | 0.15 | Α |
| h _{FE} | DC current gain | $V_{CE} = 10 \text{ V}; I_{C} = 30 \text{ mA}$ | 50 | 100 | - | |



500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2. Pinning

| I dibio L. | 9 | | |
|------------|-------------|--------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1 | base | | |
| 2 | emitter | 3 | 3 |
| 3 | collector | 1 2 | 1 — 2 |
| | | | svm021 |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| PMBTA45 | - | plastic surface-mounted package; 3 leads | SOT23 |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| PMBTA45 | LK* |

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

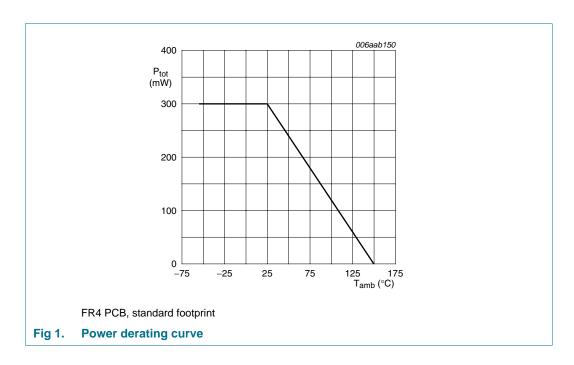
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| | | • • | , | | |
|------------------|---------------------------------------|---|--------------|------|------|
| Symbol | Parameter | Conditions | Min | Max | Unit |
| V_{CBO} | collector-base voltage | open emitter | - | 500 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 500 | V |
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0 V$ | - | 500 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 6 | V |
| I _C | collector current | | - | 0.15 | Α |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | 0.5 | Α |
| I _{BM} | peak base current | single pulse; $t_p \le 1 \text{ ms}$ | - | 200 | mA |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | <u>[1]</u> _ | 300 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | –55 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| • | · · · · · · · · · · · · · · · · · · · | | | | |

500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



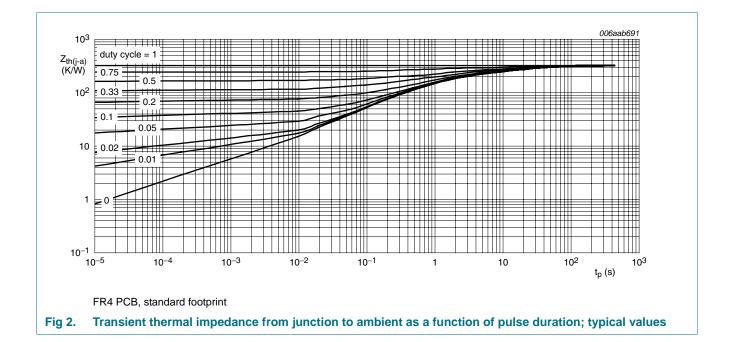
500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | <u>[1]</u> | - | - | 417 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 70 | K/W |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

7. Characteristics

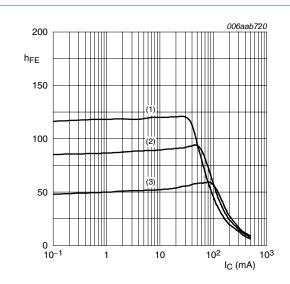
Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

| unio | | | | | | | |
|--------------------|--------------------------------------|---|-----|-----|------|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| I _{CBO} | | $V_{CB} = 360 \text{ V}; I_E = 0 \text{ A}$ | | - | - | 100 | nA |
| current | current | $V_{CB} = 360 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$ | | - | - | 10 | μΑ |
| I _{CES} | collector-emitter cut-off current | $V_{CE} = 360 \text{ V}; V_{BE} = 0 \text{ V}$ | | - | - | 100 | nA |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$ | | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 10 V | | | | | |
| | | $I_C = 30 \text{ mA}$ | | 50 | 100 | - | |
| | | I _C = 50 mA | [1] | 50 | 100 | - | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$ | | - | 60 | 75 | mV |
| sat | | $I_C = 50 \text{ mA}; I_B = 6 \text{ mA}$ | [1] | - | 65 | 90 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$ | [1] | - | 0.75 | 0.9 | V |
| f _T | transition frequency | $V_{CE} = 10 \text{ V}; I_{E} = 10 \text{ mA};$ f = 100 MHz | | - | 35 | - | MHz |
| C _c | collector capacitance | $V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz | | - | 4 | - | pF |
| C _e | emitter capacitance | $V_{EB} = 0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A}; f = 1 \text{ MHz}$ | | - | 200 | - | pF |
| t _d | delay time | $V_{CC} = 20 \text{ V}; I_C = 0.05 \text{ A};$ | | - | 80 | - | ns |
| t _r | rise time | $I_{Bon} = 5 \text{ mA};$ | | - | 2700 | - | ns |
| t _{on} | turn-on time | $I_{Boff} = -10 \text{ mA}$ | | - | 2780 | - | ns |
| t _s | storage time | | | - | 3400 | - | ns |
| t _f | fall time | | | - | 800 | - | ns |
| t _{off} | turn-off time | | | - | 4200 | - | ns |

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

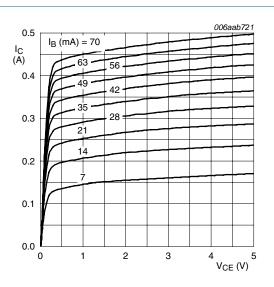
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$$V_{CE} = 10 \text{ V}$$

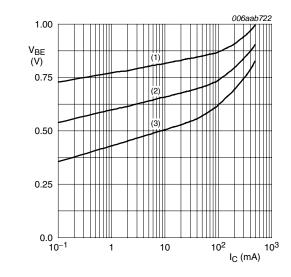
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

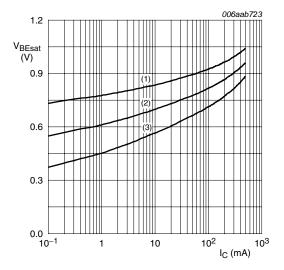
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

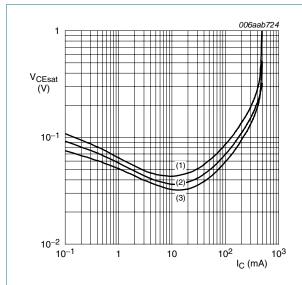


 $I_{\rm C}/I_{\rm B}=5$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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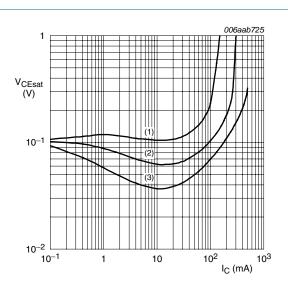
$$I_{\rm C}/I_{\rm B}=5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



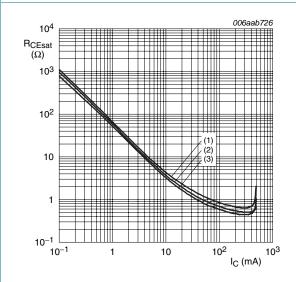
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3) $I_C/I_B = 5$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



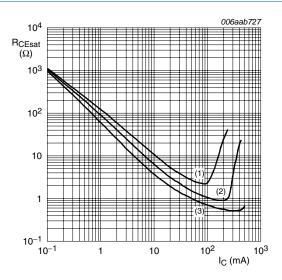
$$I_{\rm C}/I_{\rm B}=5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 20$$

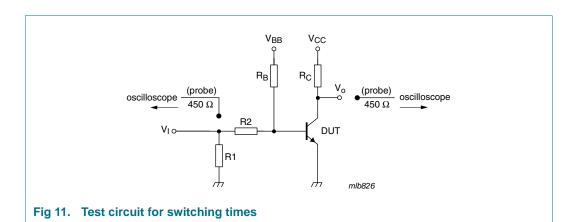
(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

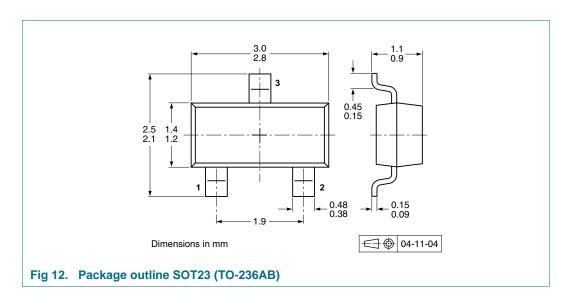
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | Packing quantity | |
|-------------|---------|--------------------------------|------------------|-------|
| | | | 3000 | 10000 |
| PMBTA45 | SOT23 | 4 mm pitch, 8 mm tape and reel | -215 | -235 |

^[1] For further information and the availability of packing methods, see Section 14.

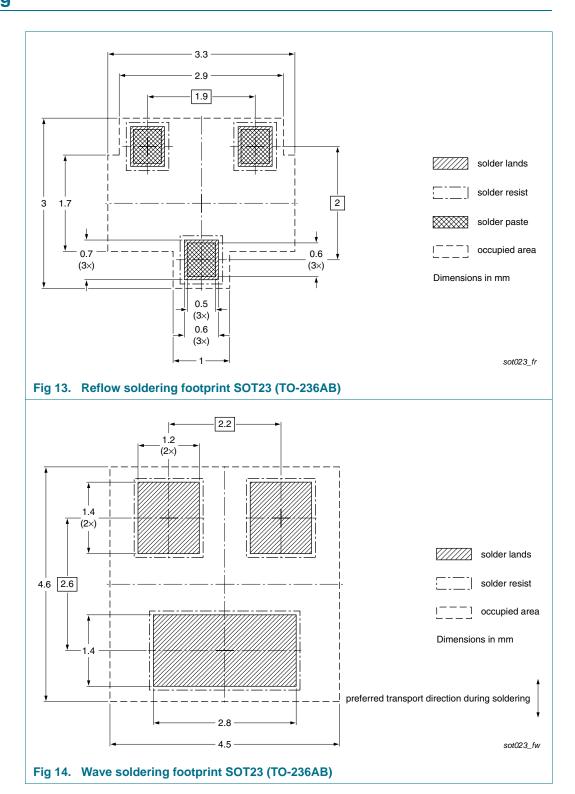
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11. Soldering



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12. Revision history

Table 9. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|----------------|--------------------|---------------|------------|
| PMBTA45_2 | 20100310 | Product data sheet | - | PMBTA45_1 |
| Modifications: | • Figure 7: up | dated | | |
| PMBTA45_1 | 20090916 | Product data sheet | - | - |

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13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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